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\$112, second paragraph, and has been amended as to form. Reconsideration and allowance of amended claim 3 are respectfully requested.

In view of the present amendment, it is believed that the present application has been placed in condition for allowance. Reconsideration and allowance are respectfully requested.

Attached hereto is a marked-up version of the changes made to the claims. The attached page is captioned "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

Respectfully submitted,

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Βv

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Claim 3 as follows:

--3. (amended) A structure of a non-volatile flash memory that is a NOR type non-volatile flash memory, provides floating gates and a common source line, wherein:

[the] <u>an</u> impurity gradient distribution of a source in a memory cell [at the] adjacent [position,] <u>to</u> where said source [joints] <u>joins</u> a semiconductor substrate[,] is [formed to be] gradual.--